

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L1	17	semiconductor adj laser and current and block\$3 and depletion and enhancement and layer	USPAT; US-PGP UB	2002/04/16 09:57			0
2	BRS	L3	1	1 and 2	USPAT; US-PGP UB	2002/04/16 10:19			0
3	BRS	L2	8	low adj carrier adj concentration adj layer and gaas	USPAT; US-PGP UB	2002/04/16 09:59			0
4	BRS	L4	9	1 and gaas	USPAT; US-PGP UB	2002/04/16 10:30			0
5	BRS	L5	0	semiconductor adj laser and gaas and depletion adj enhancement adj layer and low adj carrier adj concentration adj layer	USPAT; US-PGP UB	2002/04/16 10:34			0
6	BRS	L6	1	depletion adj enhancement adj layer	USPAT; US-PGP UB	2002/04/16 10:33			0
7	BRS	L7	1	enhancement adj depletion adj layer	USPAT; US-PGP UB	2002/04/16 10:33			0
8	BRS	L8	0	semiconductor adj laser and gaas and depletion adj layer and low adj carrier adj concentration adj layer	USPAT; US-PGP UB	2002/04/16 10:35			0
9	BRS	L9	141	semiconductor adj laser and gaas and depletion adj layer	USPAT; US-PGP UB	2002/04/16 10:51			0
10	BRS	L10	23	9 and ridge	USPAT; US-PGP UB	2002/04/16 10:35			0
11	BRS	L11	5	semiconductor adj laser and gaas and depletion adj layer and undoped adj layer and ridge	USPAT; US-PGP UB	2002/04/16 10:52			0

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6	BRS	L6	1	depletion adj enhancement adj layer	USPAT; US-PGP UB	2002/04/16 10:33			0
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8	BRS	L8	0	semiconductor adj laser and gaas and depletion adj layer and low adj carrier adj concentration adj layer	USPAT; US-PGP UB	2002/04/16 10:35			0
9	BRS	L9	141	semiconductor adj laser and gaas and depletion adj layer	USPAT; US-PGP UB	2002/04/16 13:02			0
10	BRS	L10	23	9 and ridge	USPAT; US-PGP UB	2002/04/16 12:07			0
11	BRS	L11	5	semiconductor adj laser and gaas and depletion adj layer and undoped adj layer and ridge	USPAT; US-PGP UB	2002/04/16 10:52			0
12	BRS	L12	25	gainp and gaas and block\$3 and layer and depletion	USPAT; US-PGP UB	2002/04/16 12:24			0
13	BRS	L13	1	gainp and gaas and block\$3 and layer and depletion adj layer and undoped adj layer	USPAT; US-PGP UB	2002/04/16 12:32			0
14	BRS	L14	17	gainp and gaas and block\$3 and layer and depletion and undoped	USPAT; US-PGP UB	2002/04/16 12:32			0
15	BRS	L15	18	semiconductor adj laser and gainp and depletion adj layer	USPAT; US-PGP UB	2002/04/16 13:02			0

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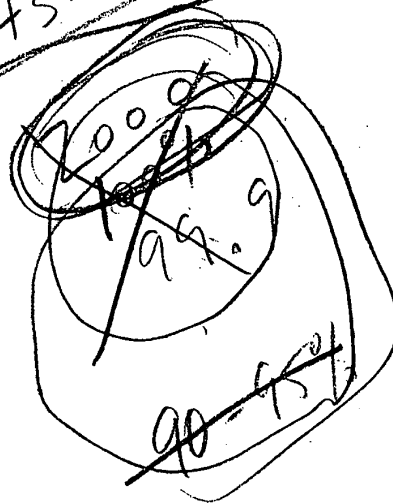
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3	BRS	L2	8	low adj carrier adj concentration adj layer and gaas	USPAT; US-PGP UB	2002/04/16 09:59			0
4	BRS	L4	9	1 and gaas	USPAT; US-PGP UB	2002/04/16 10:30			0
5	BRS	L5	0	semiconductor adj laser and gaas and depletion adj enhancement adj layer and low adj carrier adj concentration adj layer	USPAT; US-PGP UB	2002/04/16 10:34			0
6	BRS	L6	1	depletion adj enhancement adj layer	USPAT; US-PGP UB	2002/04/16 10:33			0
7	BRS	L7	1	enhancement adj depletion adj layer	USPAT; US-PGP UB	2002/04/16 10:33			0
8	BRS	L8	0	semiconductor adj laser and gaas and depletion adj layer and low adj carrier adj concentration adj layer	USPAT; US-PGP UB	2002/04/16 10:35			0
9	BRS	L9	141	semiconductor adj laser and gaas and depletion adj layer	USPAT; US-PGP UB	2002/04/16 13:02			0
10	BRS	L10	23	9 and ridge	USPAT; US-PGP UB	2002/04/16 12:07			0
11	BRS	L11	5	semiconductor adj laser and gaas and depletion adj layer and undoped adj layer and ridge	USPAT; US-PGP UB	2002/04/16 10:52			0
12	BRS	L12	25	gainp and gaas and block\$3 and layer and depletion	USPAT; US-PGP UB	2002/04/16 12:24			0
13	BRS	L13	1	gainp and gaas and block\$3 and layer and depletion adj layer and undoped adj layer	USPAT; US-PGP UB	2002/04/16 12:32			0
14	BRS	L14	17	gainp and gaas and block\$3 and layer and depletion and undoped	USPAT; US-PGP UB	2002/04/16 12:32			0
15	BRS	L15	18	semiconductor adj laser and gainp and depletion adj layer	USPAT; US-PGP UB	2002/04/16 13:02			0
16	BRS	L16	230	semiconductor adj laser and deplet\$3 adj layer	USPAT; US-PGP UB	2002/04/16 13:50			0
17	BRS	L17	7	16 and modulat\$3 adj dop\$3	USPAT; US-PGP UB	2002/04/16 13:52			0

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372/43-50 scs. +



Active

Lowest	
Lower	Depletion
Low	cladding
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